

DD3X062J0L

Silicon epitaxial planar type

For surge absorption circuit

■ Features

- Low terminal capacitance Ct
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol 51

■ Basic Part Number :

Dual DD2S062 (Common anode)

■ Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

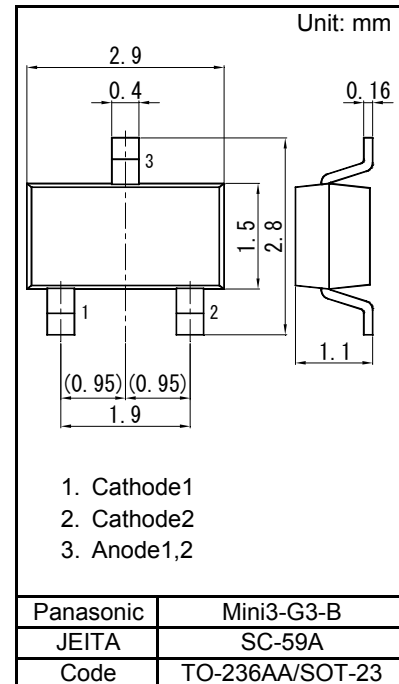
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation ^{*1}	PT	200	mW
Electrostatic discharge ^{*2}	ESD	±15	kV
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

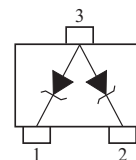
Note) *1: PT = 200 mW achieved with a printed circuit board.

(2 Diode total)

*2: Test method:IEC61000_4_2(C = 150 pF,R = 330 Ω, Contact discharge:10 times)



Internal Connection



■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage ^{*1, *2}	VZ	IZ = 5 mA	5.90		6.50	V
Zener operating resistance	RZ	IZ = 5 mA			30	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			100	Ω
Reverse current	IR	VR = 5.5 V			3	μA
Temperature coefficient of zener voltage ^{*3}	SZ	IZ = 5 mA		2.5		mV/°C
Terminal Capacitance	Ct	VR = 0 V, f = 1 MHz		10		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. *1: The temperature must be controlled 25°C for VZ measurement.

VZ value measured at other temperature must be adjusted to VZ (25°C)

*2: VZ guaranteed 20 ms after current flow.

*3: Tj = 25°C to 150°C